

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

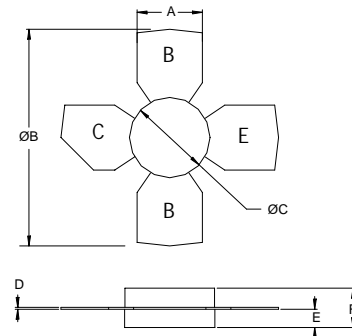
The **ASI MRF1004MB** is Designed for Class B and C, TACAN, IFF, and DME Applications up to 1090 MHz.

FEATURES:

- Class B and C Operation
- Common Base
- $P_G = 10$ dB at 4.0 W/1090 MHz
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	250 mA
V_{CE}	20 V
P_{DISS}	7.0 W @ $T_C = 25^\circ\text{C}$
T_J	-65°C to $+200^\circ\text{C}$
T_{STG}	-65°C to $+150^\circ\text{C}$
θ_{JC}	25.0 $^\circ\text{C}/\text{W}$

PACKAGE STYLE .280 4L PILL


DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.220 / 5.59	.230 / 5.84
B		1.055 / 26.80
C	.275 / 6.99	.285 / 7.24
D	.004 / 0.10	.006 / 0.15
E	.050 / 1.27	.060 / 1.52
F	.118 / 3.00	.130 / 3.30

CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	$I_C = 5.0$ mA	50			V
BV_{CEO}	$I_C = 5.0$ mA	20			V
BV_{EBO}	$I_E = 1.0$ mA	3.5			V
I_{CBO}	$V_{CB} = 35$ V			0.5	mA
h_{FE}	$V_{CE} = 5.0$ V $I_C = 75$ mA	10		100	---
P_G	$V_{CC} = 35$ V $P_{OUT} = 4.0$ W $f = 1090$ MHz	10	11		dB
η_C		40	45		%